vides for a combination of massively parallel neural-computing interconnections and mixed-signal (a combination of analog and digital) circuitry characterized by feature sizes in the deep-submicron range, making it possible to implement the ANN as a single VLSI chip. One notable aspect of the design is the use of a parallel row/column data-flow architecture to connect all on-chip subsystems and eliminate data-flow bottlenecks of the type caused by bandwidth limitations in conventional data buses.

The ANN includes input neurons, programmable-weight synapses, summing and inner product cells, output neurons, and an output multi-winner-take-all encoder. The programmable synapse matrix is composed of $M \times N$ cells for $N \times M$-dimensional code vectors. There are N output summing neurons that execute a sigmoid-logarithmic (in contradistinction to a conventional sigmoid) transfer function. The synaptic weights are generated by an error-back-propagation supervised-learning algorithm executed by an off-chip host controlling processor. The outputs of the output summing neurons are fed to a multi-winner-take-all block that consists of N competitive circuit cells and uses binary codes to encode N classes.

This work was done by Wai-Chi Fang of Caltech and Jaw-Chyng Lue of University of Southen California for NASA's Jet Propulsion Laboratory. Further information is contained in a TSP (see page 1).

In accordance with Public Law 96-517, the contractor has elected to retain title to this invention. Inquiries concerning rights for its commercial use should be addressed to:

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Refer to NPO-44155, volume and number of this NASA Tech Briefs *issue, and the page number.*

Low-Noise Amplifier for 100 to 180 GHz

Noise temperature is lower than in the prior state of the art.

NASA's Jet Propulsion Laboratory, Pasadena, California

A three-stage monolithic millimeter-wave integrated-circuit (MMIC) amplifier designed to exhibit low noise in operation at frequencies from about 100 to somewhat above 180 GHz has been built and tested. This is a prototype of broadband amplifiers that have potential utility in diverse applications, including measurement of atmospheric temperature and humidity and millimeter-wave imaging for inspecting contents of opaque containers.

Figure 1 depicts the amplifier as it appears before packaging. Figure 2 presents data from measurements of the performance of the amplifier as packaged in a WR-05 waveguide and tested in the frequency range from about 150 to about 190 GHz. The amplifier exhibited substantial gain throughout this frequency range. Especially notable is the fact that at 165 GHz, the noise figure was found to be 3.7 dB, and the noise temperature was found to be 370 K: This is less than half the noise temperature of the prior state of the art.

This work was done by Pekka Kangaslahti, David Pukala, King Man Fung, and Todd Gaier of Caltech and Xiaobing Mei, Richard Lai, and William Deal of Northrop Grumman Corporation for NASA's Jet Propulsion Laboratory. For more information, contact iaoffice@jpl.nasa.gov. NPO-45178

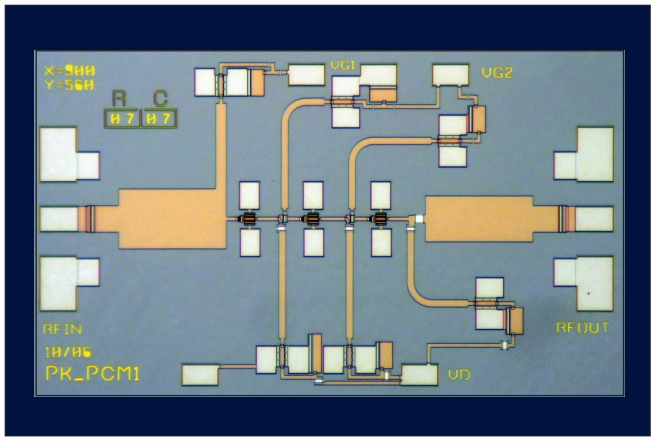

Figure 1. This **MMIC Amplifier** includes InP high-electron-mobility transistors (HEMTs) connected to microstrip transmission lines on a substrate of 2-mil (≈51-μm) thickness. Each HEMT has two fingers and a gate width of 15 μm, for a total gate periphery of 30 μm.

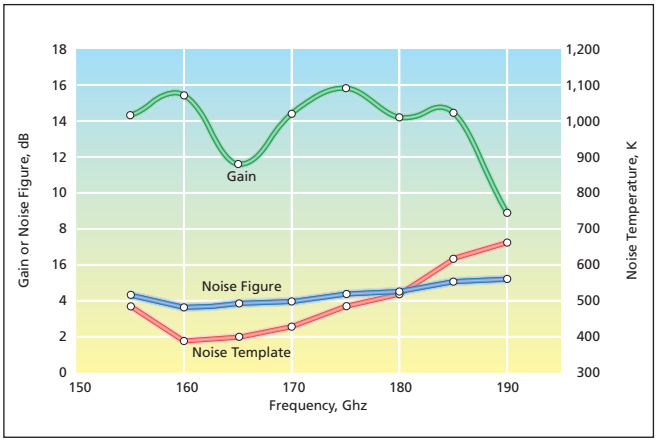

Figure 2. These **Plots of Performance Data** were derived from measurements on the amplifier as packaged in a WR-05 waveguide [a waveguide having a cross section of 0.0510 by 0.0255 in. (about 1.30 by 0.65 mm), nominally for the frequency range of 140 to 220 GHz].